

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D $T_C = +25^\circ C$
60V	4.8m Ω @ $V_{GS} = 10V$	77.8A
	6.5m Ω @ $V_{GS} = 4.5V$	68.2A

Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$ —Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact_us) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Description and Applications

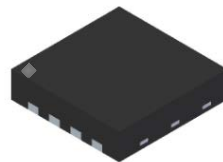
This new generation N-channel enhancement mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and load switch.

- Synchronous Rectifier
- Power Management Functions
- DC-DC Converters

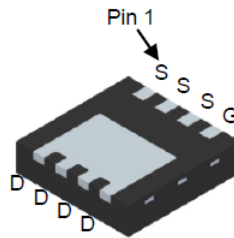
Mechanical Data

- Case: V-DFN3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Below Diagram
- Terminals: Finish—NiPdAu over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 E4
- Weight: 0.027 grams (Approximate)

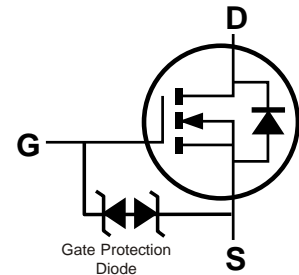
V-DFN3333-8 (Type B)



Top View



Bottom View



Equivalent Circuit

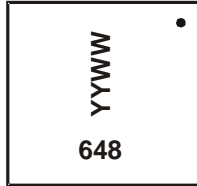
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT64M8LCG-7	V-DFN3333-8 (Type B)	2,000/Tape & Reel
DMT64M8LCG-13	V-DFN3333-8 (Type B)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

Site 1:



648 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 20 = 2020)
 WW = Week (01 to 53)

Site 2:



648 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 0 = 2020)
 W = Week (ex: a = week 27; z represents week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	9	0	1	2	3	4	5	6	7	8	9	0
Week	1-26				27-52				53			
Code	A-Z				a-z				z			
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	I_D	$T_A = +25^\circ\text{C}$	16.1
		$T_A = +70^\circ\text{C}$	12.9
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 7)	I_D	$T_C = +25^\circ\text{C}$	77.8
		$T_C = +70^\circ\text{C}$	62.2
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	310	A
Maximum Continuous Body Diode Forward Current (Note 7)	I_S	77	A
Pulsed Body Diode Forward Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	310	A
Avalanche Current, $L = 0.3\text{mH}$	I_{AS}	27.2	A
Avalanche Energy, $L = 0.3\text{mH}$	E_{AS}	111	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.99	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	126	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	P_D	2.16	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	58	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.3	—	2.4	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.8	4.8	m Ω	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	4.8	6.5		$V_{GS} = 4.5\text{V}, I_D = 12.5\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	2664	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	955	—		
Reverse Transfer Capacitance	C_{rss}	—	75	—		
Gate Resistance	R_g	—	0.76	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	26.1	—	nC	$V_{DS} = 30\text{V}, I_D = 20\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	47.5	—		
Gate-Source Charge	Q_{gs}	—	6.2	—		
Gate-Drain Charge	Q_{gd}	—	12.5	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.4	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, I_D = 20\text{A}, R_G = 3.3\Omega$
Turn-On Rise Time	t_R	—	9.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	29.8	—		
Turn-Off Fall Time	t_F	—	18.3	—		
Reverse Recovery Time	t_{RR}	—	41	—	ns	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	53	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

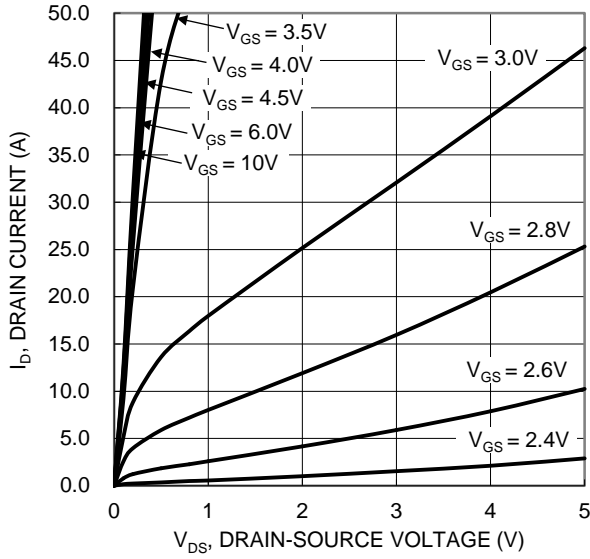


Figure 1. Typical Output Characteristic

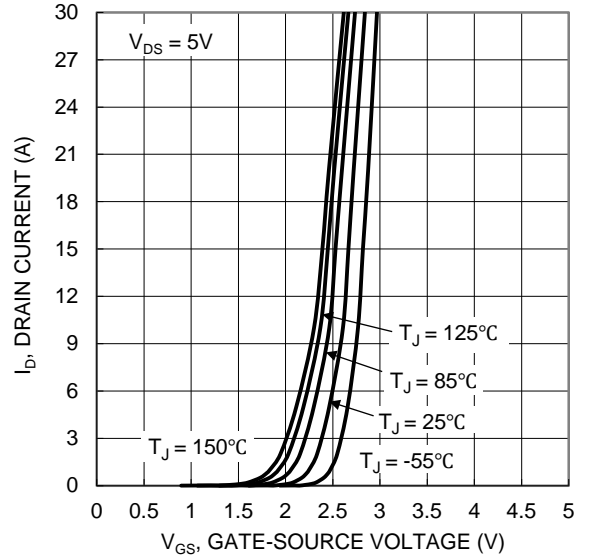


Figure 2. Typical Transfer Characteristic

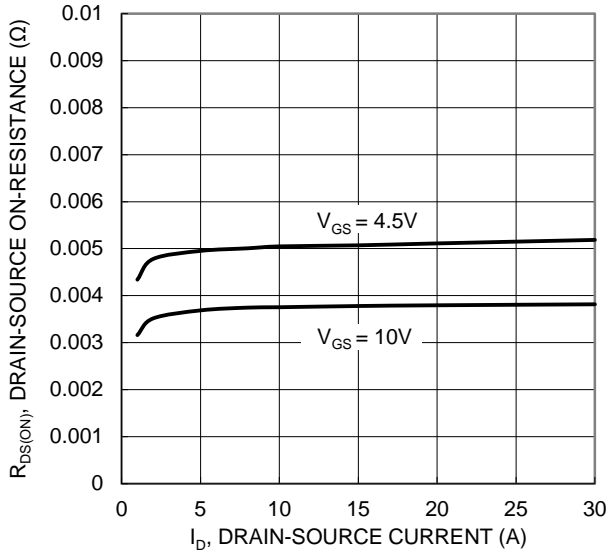


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

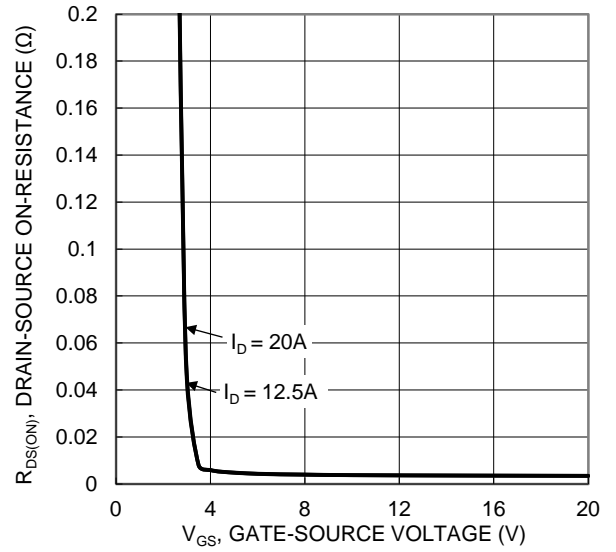


Figure 4. Typical Transfer Characteristic

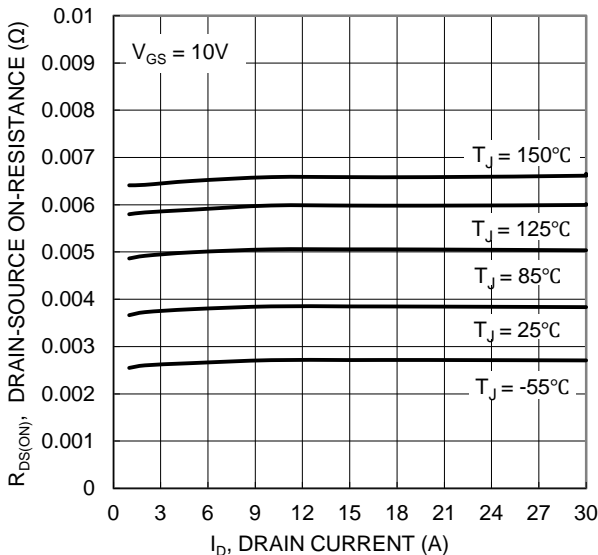


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

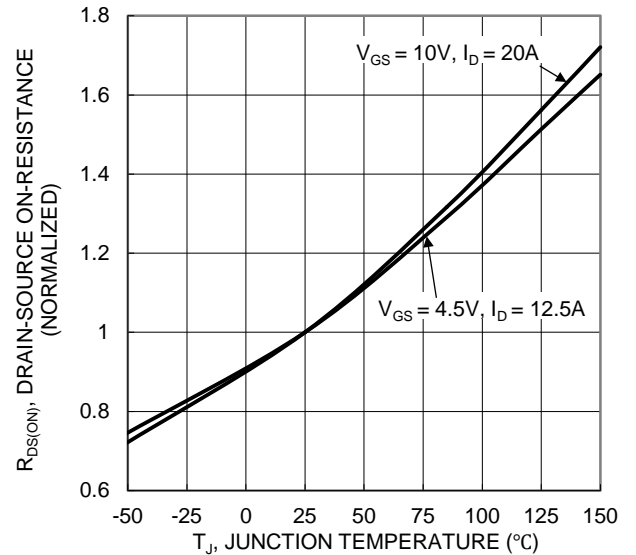


Figure 6. On-Resistance Variation with Junction Temperature

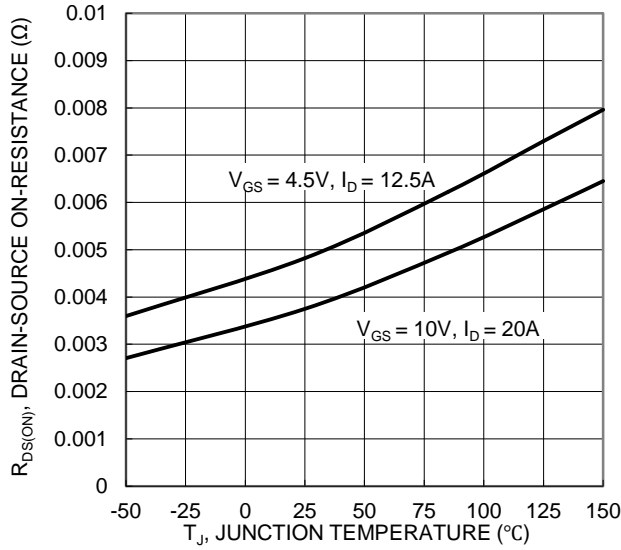


Figure 7. On-Resistance Variation with Junction Temperature

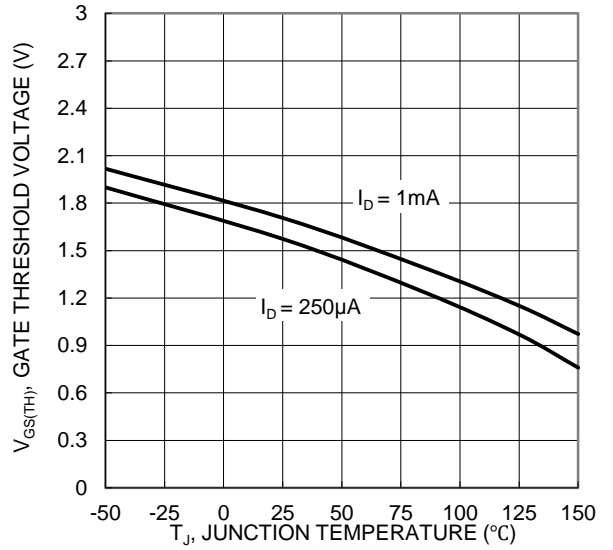


Figure 8. Gate Threshold Variation vs. Junction Temperature

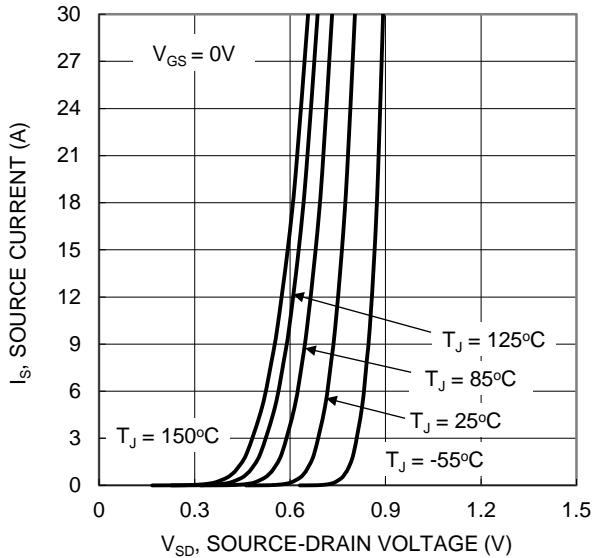


Figure 9. Diode Forward Voltage vs. Current

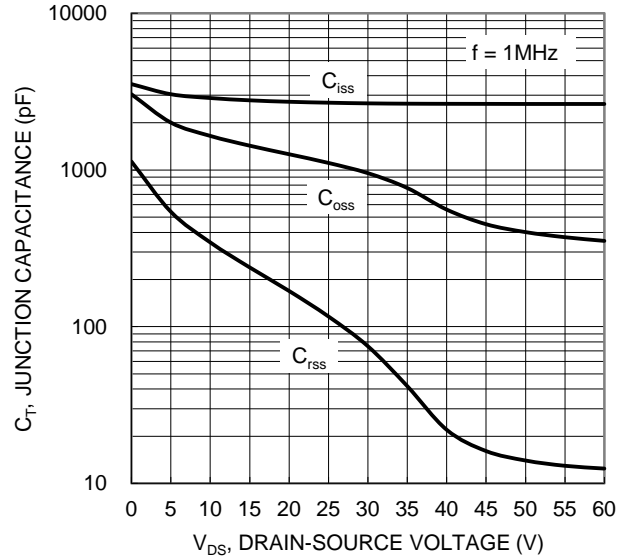


Figure 10. Typical Junction Capacitance

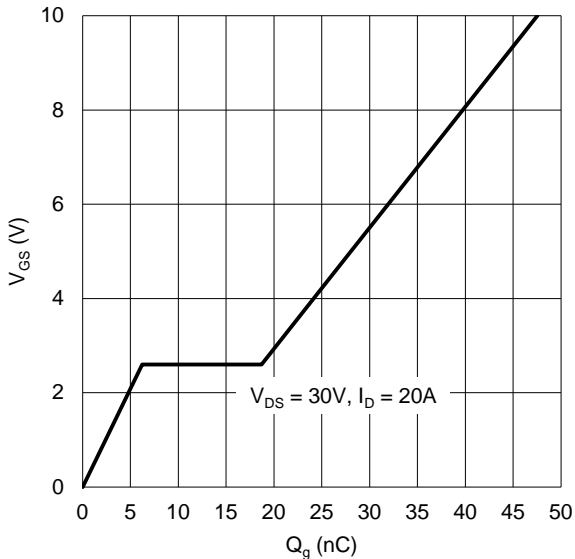


Figure 11. Gate Charge

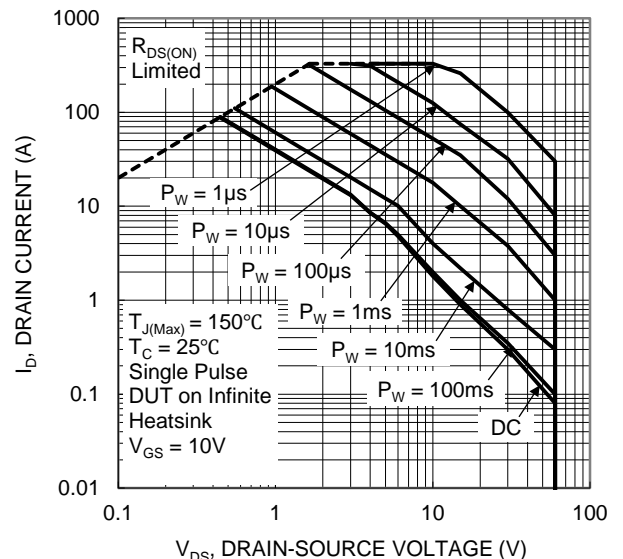


Figure 12. SOA, Safe Operation Area

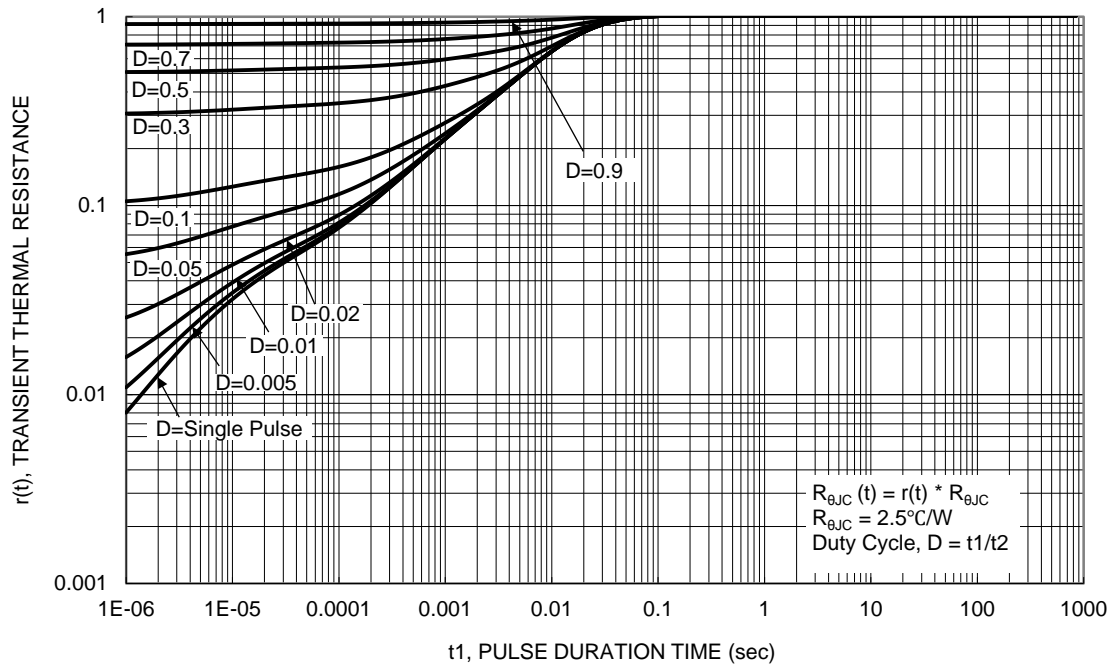
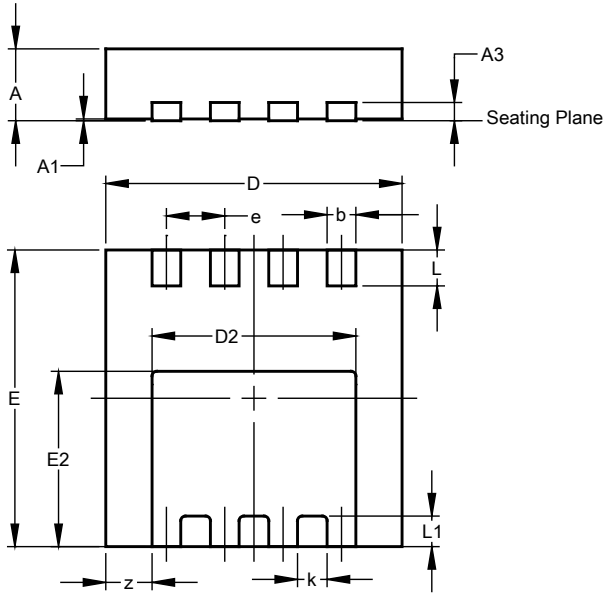


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

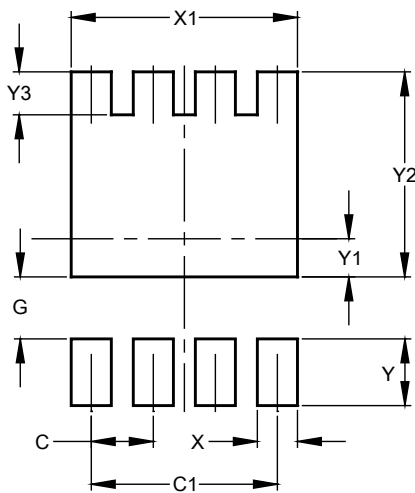
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



V-DFN3333-8 (Type B)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	--	--	0.203
b	0.27	0.37	0.32
D	3.25	3.35	3.30
D2	2.17	2.37	2.27
E	3.25	3.35	3.30
E2	1.85	2.05	1.95
e	--	--	0.65
k	--	--	0.33
L	0.35	0.45	0.40
L1	--	--	0.34
z	--	--	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.650
C1	1.950
G	0.650
X	0.420
X1	2.370
Y	0.700
Y1	0.400
Y2	2.150
Y3	0.450

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